Takashi Kita

List of Publications by Year
in descending order

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270	3,665	159358	182168
papers	citations	30	51
		h-index	g-index

272	272	272	2222
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Yb-doped Yâ€“Alâ€“O thin films with a self-organized columnar structure and their anti-Stokes photoluminescence properties. AIP Advances, 2022, 12, .	0.6	1
2	Two-step excitation induced photovoltaic properties in an InAs quantum dot-in-well intermediate-band solar cell. Journal of Applied Physics, 2021, 129, .	1.1	5
3	Collection of Photocarriers Varied by Effective Electron Intraband Excitation in an InAs Quantum Dot-in-Well Intermediate Band Solar Cell. , 2021, , .		0
4	Modulation of exciton states through resonant excitation by continuous wave lasers in a GaAs/AlAs multiple quantum well. Journal Physics D: Applied Physics, 2021, 54, 335106.	1.3	1
5	Increase in terahertz-wave generation by difference frequency mixing by the overlap of exciton states in different GaAs/AlAs quantum wells and spectroscopic measurements. Optics Express, 2021, 29, 24387.	1.7	4
6	Voltage boost effects in two-step photon upconversion solar cells with a modulation-doped structure. Journal of Applied Physics, 2021, 130, 085701.	1.1	2
7	Two-photon photocurrent spectra of InAs quantum dot-in-well intermediated-band solar cells at room temperature. Journal of Applied Physics, 2021, 130, .	1.1	2
8	Infrared photodetector sensitized by InAs quantum dots embedded near an Al0.3Ga0.7As/GaAs heterointerface. Scientific Reports, 2020, 10, 11628.	1.6	19
9	Electron transport in a silicon crystal observed by energy transfer luminescence. Japanese Journal of Applied Physics, 2020, 59, 082005.	0.8	1
10	Reciprocal Relation Between Intraband Carrier Generation and Interband Recombination at the Heterointerface of Two-Step Photon Up-Conversion Solar Cells. Physical Review Applied, 2020, 14, .	1.5	4
11	Resonant exciton excitation photoluminescence and dynamics in a GaAs/AlAs multiple quantum well with internal electric field. AIP Advances, 2020, 10, .	0.6	8
12	Determination of silicon wafer site flatness using dual heterodyne interferometers with sub-nanometer precision. Review of Scientific Instruments, 2020, 91, 065114.	0.6	3
13	Polarization-insensitive fiber-to-fiber gain of semiconductor optical amplifier using closely stacked InAs/GaAs quantum dots. Japanese Journal of Applied Physics, 2020, 59, 032002.	0.8	6
14	An energy transfer accompanied by phonon absorption in ytterbium-doped yttrium aluminum perovskite for optical refrigeration. Applied Physics Letters, 2020, 117, .	1.5	3
15	Properties of Anti-Stokes Photoluminescence and Ideal Laser Cooling Performance in Yb-Doped Yttrium Aluminum Garnet Thin Film. Zairyo/Journal of the Society of Materials Science, Japan, 2020, 69, 727-732.	0.1	1
16	Wide-wavelength-range control of photoluminescence polarization in closely stacked InAs/GaAs quantum dots. Journal of Applied Physics, 2019, 125, .	1.1	5
17	Exciton dynamics as a function of excitation intensity and double-pulse excitation in cyanine molecule thin films: Toward low-power optical switches. Journal of Applied Physics, 2019, 126, 033103.	1.1	1
18	Actual Calculation of Solar Cell Efficiencies. Green Energy and Technology, 2019, , 81-137.	0.4	0

#	Article	IF	Citations
19	Hot-carrier generation and extraction in InAs/GaAs quantum dot superlattice solar cells. Semiconductor Science and Technology, 2019, 34, 094003.	1.0	13
20	Energy Conversion Efficiency of Solar Cells. Green Energy and Technology, 2019, , .	0.4	10
21	Ideal Laser Cooling Efficiency Utilizing Anti-Stokes Luminescence in Yb-Doped Yttrium Aluminum Garnet Powder Crystals. Zairyo/Journal of the Society of Materials Science, Japan, 2019, 68, 762-766.	0.1	0
22	Adiabatic two-step photoexcitation effects in intermediate-band solar cells with quantum dot-in-well structure. Scientific Reports, 2019, 9, 7859.	1.6	12
23	Reply to: â€œThermal artefacts in two-photon solar cell experimentsâ€• Nature Communications, 2019, 10, 956.	5.8	8
24	Reciprocal relationship between photoluminescence and photocurrent in two-step photon up-conversion solar cell. , 2019, , .		0
25	Hot-Carrier Extraction in InAs/GaAs Quantum Dot Superlattice Solar Cells. , 2019, , .		1
26	Bound-to-continuum intraband transition properties in InAs/GaAs quantum dot superlattice solar cells. Applied Physics Express, 2019, 12, 125008.	1.1	2
27	Improving laser cooling efficiencies of Yb-doped yttrium aluminum garnet by utilizing non-resonant anti-Stokes emission at high temperatures. Optics Express, 2019, 27, 34961.	1.7	7
28	Effects of a thin nitrogen-doped layer on terahertz dynamics in GaAs containing InAs quantum dots. OSA Continuum, 2019, 2, 1621.	1.8	0
29	Optical Response of Two-Dimensional Photonic Crystal on Metal. Zairyo/Journal of the Society of Materials Science, Japan, 2019, 68, 757-761.	0.1	0
30	Increasing conversion efficiency of two-step photon up-conversion solar cell with a voltage booster hetero-interface. Scientific Reports, 2018, 8, 872.	1.6	15
31	Two-step photocurrent generation enhanced by the fundamental-state miniband formation in intermediate-band solar cells using a highly homogeneous InAs/GaAs quantum-dot superlattice. Applied Physics Express, 2018, 11, 012301.	1.1	4
32	Carrier collection efficiency of intraband-excited carriers in two-step photon up-conversion solar cells. , 2018, , .		0
33	Development of mercury-free ultraviolet light emitting devices. , 2018, , .		0
34	Wide Frequency Tuning of Continuous Terahertz Wave Generated by Difference Frequency Mixing under Exciton-Excitation Conditions in a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Ga</mml:mi><mml:mi>As</mml:mi></mml:math> / <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Al</mml:mi><mml:mi>As</mml:mi></mml:math> Multiple Quantum Well. p	1.5	6
35	Effect of lattice-mismatch strain on electron dynamics in InAs/GaAs quantum dots as seen by time-domain terahertz spectroscopy. Journal Physics D: Applied Physics, 2018, 51, 305102.	1.3	3
36	Hot-carrier generation in a solar cell containing InAs/GaAs quantum-dot superlattices as a light absorber. Applied Physics Express, 2018, 11, 082303.	1.1	5

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37	Two-step photon up-conversion solar cell: propose and demonstration. , 2018, , .		1
38	Effects of non-exciton components excited by broadband pulses on quantum beats in a GaAs/AlAs multiple quantum well. Scientific Reports, 2017, 7, 41496.	1.6	5
39	Two-step photocurrent generation enhanced by miniband formation in InAs/GaAs quantum dot superlattice intermediate-band solar cells. Applied Physics Letters, 2017, 110, .	1.5	8
40	Two-step photon up-conversion solar cells. Nature Communications, 2017, 8, 14962.	5.8	88
41	Ferromagnetic resonance features of degenerate GdN semiconductor. Physics Letters, Section A: General, Atomic and Solid State Physics, 2017, 381, 1905-1909.	0.9	2
42	Excitation of Thin Cyanine Films via Energy Transfer from Si Substrate. Journal of the Physical Society of Japan, 2017, 86, 094710.	0.7	1
43	Efficient two-step photocarrier generation in bias-controlled InAs/GaAs quantum dot superlattice intermediate-band solar cells. Scientific Reports, 2017, 7, 5865.	1.6	17
44	Spatially resolved electronic structure of an isovalent nitrogen center in GaAs. Physical Review B, 2017, 96, .	1.1	8
45	Recent Advancement of Semiconductor Materials and Devices. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 244-249.	0.1	0
46	Fundamental Device Characteristics of Hot Carrier Solar Cell Using InAs/GaAs Quantum Dot Superlattices.. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 629-633.	0.1	0
47	Effects of exciton line widths on the amplitude of quantum beat oscillations. Applied Physics Express, 2016, 9, 062801.	1.1	3
48	Increase in exciton decay rate due to plane-to-plane interaction between cyanine thin films. AIP Advances, 2016, 6, 075209.	0.6	3
49	Polarization characteristics of electroluminescence and net modal gain in highly stacked InAs/GaAs quantum-dot laser devices. Journal of Applied Physics, 2016, 120, .	1.1	3
50	Effects of rapid thermal annealing on two-dimensional delocalized electronic states of the epitaxial N Î´-doped layer in GaAs. Applied Physics Letters, 2016, 108, 111905.	1.5	4
51	Photocarrier transport dynamics in InAs/GaAs quantum dot superlattice solar cells using time-of-flight spectroscopy. Physical Review B, 2016, 94, .	1.1	7
52	Emission-wavelength tuning of InAs quantum dots grown on nitrogen-Î´-doped GaAs(001). Journal of Applied Physics, 2016, 119, 194306.	1.1	6
53	Effective drift mobility approximation in multiple quantum-well solar cell. , 2016, , .		4
54	Polarization anisotropy of electroluminescence and net-modal gain in highly stacked InAs/GaAs quantum-dot laser devices. , 2016, , .		0

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55	Nanosecond-scale hot-carrier cooling dynamics in one-dimensional quantum dot superlattices. Physical Review B, 2016, 93, .	1.1	19
56	Two-dimensional energy dispersion in thermally annealed epitaxial nitrogen atomic sheet in GaAs. , 2016, , .		0
57	Organic-Lead Halide Perovskite Solar Cell with ITO Transparent Electrode Deposited by Sputtering Process. Zairyo/Journal of the Society of Materials Science, Japan, 2016, 65, 642-646.	0.1	0
58	Saturable Two-Step Photocurrent Generation in Intermediate-Band Solar Cells Including InAs Quantum Dots Embedded in Al_{0.3}Ga_{0.7}/GaAs Quantum Wells. IEEE Journal of Photovoltaics, 2016, 6, 465-472.	1.5	23
59	Rapid dephasing related to intersubband transitions induced by exciton quantum beats observed by a pump-probe technique in a GaAs/AlAs multiple quantum well. Physical Review B, 2015, 91, .	1.1	4
60	Two-step photon absorption in InAs/GaAs quantum-dot superlattice solar cells. Physical Review B, 2015, 91, .	1.1	35
61	Broadband control of emission wavelength of InAs/GaAs quantum dots by GaAs capping temperature. Journal of Applied Physics, 2015, 118, .	1.1	24
62	Microscopic observation of carrier-transport dynamics in quantum-structure solar cells using a time-of-flight technique. Applied Physics Letters, 2015, 107, .	1.5	13
63	Two-step photocarrier generation in InAs/GaAs quantum dot superlattice intermediate band solar cell. , 2015, , .		0
64	Saturable two-step photocurrent generation in intermediate-band solar cells including InAs quantum dots embedded in Al0.3Ga0.7As/GaAs quantum wells. , 2015, , .		0
65	Comparison of electron and hole mobilities in multiple quantum well solar cells using a time-of-flight technique. , 2015, , .		0
66	Ultrafast photocarrier transport dynamics in InAs/GaAs quantum dot superlattice solar cell. , 2015, , .		0
67	Fabrication of cyanine dye thin films grown by a layer-by-layer method. Materials Research Express, 2015, 2, 076402.	0.8	4
68	Intermediate band solar cells: Recent progress and future directions. Applied Physics Reviews, 2015, 2, 021302.	5.5	314
69	Suppression of thermal carrier escape and enhanced two-step photon absorption in quantum-dot intermediate-band solar cells with a high-potential barrier. , 2015, , .		0
70	Microscopic properties of degradation-free capped GdN thin films studied by electron spin resonance. Journal of Applied Physics, 2015, 117, 043909.	1.1	4
71	Thermal annealing effects on ultra-violet luminescence properties of Gd doped AlN. Journal of Applied Physics, 2015, 117, 163105.	1.1	12
72	Comparison of Electron and Hole Mobilities in Multiple-Quantum-Well Solar Cells Using a Time-of-Flight Technique. IEEE Journal of Photovoltaics, 2015, 5, 1613-1620.	1.5	12

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73	Analysis of Optical Waveguide Mode in Closely-Stacked InAs/GaAs Quantum Dot Semiconductor Optical Amplifiers. Zairyo/Journal of the Society of Materials Science, Japan, 2015, 64, 685-689.	0.1	0
74	Pulse modulation towards low-power operation based on the quantum beat of excitons in a GaAs/AlAs multiple quantum well. Journal Physics D: Applied Physics, 2014, 47, 105101.	1.3	5
75	Polarization-insensitive optical gain characteristics of highly stacked InAs/GaAs quantum dots. Journal of Applied Physics, 2014, 115, .	1.1	15
76	Control of optical properties in cyanine dye thin film fabricated by a layer-by-layer method. Journal of Applied Physics, 2014, 115, 083503.	1.1	6
77	Electronic transitions in GdN band structure. Journal of Applied Physics, 2014, 115, .	1.1	9
78	Resonant indirect excitation of Gd3+ in AlN thin films. Journal of Applied Physics, 2014, 115, 173508.	1.1	2
79	Effect of internal electric field on InAs/GaAs quantum dot solar cells. Journal of Applied Physics, 2014, 115, 083510.	1.1	31
80	Hot-carrier solar cells using low-dimensional quantum structures. Applied Physics Letters, 2014, 105, 171904.	1.5	17
81	Carrier Time-of-Flight Measurement Using a Probe Structure for Direct Evaluation of Carrier Transport in Multiple Quantum Well Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 1518-1525.	1.5	13
82	Effect of exciton oscillator strength on upconversion photoluminescence in GaAs/AlAs multiple quantum wells. Applied Physics Letters, 2014, 105, .	1.5	8
83	Epitaxial two-dimensional nitrogen atomic sheet in GaAs. Applied Physics Letters, 2014, 104, .	1.5	15
84	Suppression of thermal carrier escape and efficient photo-carrier generation by two-step photon absorption in InAs quantum dot intermediate-band solar cells using a dot-in-well structure. Journal of Applied Physics, 2014, 116, .	1.1	31
85	Intermediate band photovoltaics based on interbandâ€“intraband transitions using In_{0.53}Ga_{0.47}As/InP superlattice. Progress in Photovoltaics: Research and Applications, 2013, 21, 472-480.	4.4	12
86	Tuning optical and ferromagnetic properties of thin GdN films by nitrogen-vacancy centers. European Physical Journal B, 2013, 86, 1.	0.6	9
87	Polarization controlled emisson from closely stacked InAs/GaAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1492-1495.	0.8	2
88	Carrier dynamics in intermediate states of InAs/GaAs quantum dots embedded in photonic cavity structure. , 2013, , .		0
89	Carrier dynamics in intermediate states of InAs/GaAs quantum dots embedded in photonic cavity structure. , 2013, , .		0
90	Enhancement of Optical Anisotropy by Interconnection Effect along Growth Direction in Multistacked Quantum Dots. Japanese Journal of Applied Physics, 2013, 52, 012001.	0.8	0

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91	Evaluation of minority and majority spin band energies of ferromagnetic GdN thin film using optical absorption spectroscopy. , 2013, , .		1
92	One-dimensional miniband formation in closely stacked InAs/GaAs quantum dots. Physical Review B, 2013, 87, .	1.1	47
93	Giant optical splitting in the spin-states assisting a sharp magnetic switching in GdN thin films. Applied Physics Letters, 2013, 102, .	1.5	9
94	Control of stacking direction and optical anisotropy in InAs/GaAs quantum dots by In flux. Journal of Applied Physics, 2013, 114, .	1.1	6
95	Effects of pumping on propagation velocities of confined exciton polaritons in GaAs/AlxGa1â^'xAs double heterostructure thin films under resonant and non-resonant probe conditions. Journal of Applied Physics, 2013, 113, 013514.	1.1	1
96	Intraband carrier dynamics in InAs/GaAs quantum dots stimulated by bound-to-continuum excitation. Journal of Applied Physics, 2013, 113, .	1.1	25
97	Magneto-optical effect in GdN epitaxial thin film. Journal of Physics: Conference Series, 2013, 417, 012053.	0.3	3
98	Correlation between local atomic structure and ultraviolet luminescence of AlGdN thin films. Journal of Physics: Conference Series, 2013, 417, 012049.	0.3	2
99	Atomically Controlled Growth of Self-Assembled Quantum Dots and Realization of Highly Functional Optical Responses. Journal of Smart Processing, 2013, 2, 206-212.	0.0	0
100	Study on spin-splitting phenomena in the band structure of GdN. Applied Physics Letters, 2012, 100, .	1.5	22
101	Ferromagnetic properties of GdN thin films studied by temperature dependent circular polarized spectroscopy. Applied Physics Letters, 2012, 101, 072403.	1.5	11
102	Multiple excitation process in deep-ultraviolet emission from AlGdN thin films pumped by an electron beam. Journal of Applied Physics, 2012, 111, 083526.	1.1	4
103	Observation of quantum beat oscillations and ultrafast relaxation of excitons confined in GaAs thin films by controlling probe laser pulses. Journal of Applied Physics, 2012, 111, 023505.	1.1	12
104	Transient photoconductivity responses in amorphous In-Ga-Zn-O films. Journal of Applied Physics, 2012, 112, 053715.	1.1	42
105	High-resolution optical coherence tomography using broadband light source with strain-controlled InAs/GaAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2473-2476.	0.8	1
106	Carrier dynamics in intermediate states of InAs/GaAs quantum dots embedded in photonic cavity structure. , 2012, , .		0
107	Effect of spacer layer thickness on multi-stacked InGaAs quantum dots grown on GaAs (311)B substrate for application to intermediate band solar cells. Journal of Applied Physics, 2012, 111, 074305.	1.1	23
108	Carrier dynamics of the intermediate state in InAs/GaAs quantum dots coupled in a photonic cavity under two-photon excitation. Physical Review B, 2012, 86, .	1.1	30

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109	Nearâ€field photoluminescence spectroscopy of CdTe/Cd_{0.75}Mn_{0.25}Te tilted superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 262-265.	0.8	0
110	Quantum Dot Switches: Towards Nanoscale Power-Efficient All-Optical Signal Processing. , 2012, , 197-221.		1
111	Increase in photocurrent by optical transitions via intermediate quantum states in direct-doped InAs/GaNAs strain-compensated quantum dot solar cell. Journal of Applied Physics, 2011, 109, .	1.1	216
112	Suppression of nonradiative recombination process in directly Si-doped InAs/GaAs quantum dots. Journal of Applied Physics, 2011, 110, 103511.	1.1	25
113	Extremely uniform bound exciton states in nitrogen Î´-doped GaAs studied by photoluminescence spectroscopy in external magnetic fields. Journal of Applied Physics, 2011, 110, 083522.	1.1	10
114	Ferromagnetic State of GdN Thin Film Studied by Ferromagnetic Resonance. AIP Conference Proceedings, 2011, , .	0.3	1
115	Magneto-Photoluminescence Spectroscopy of Exciton Fine Structure in Nitrogen Î´-Doped GaAs. AIP Conference Proceedings, 2011, , .	0.3	0
116	Saturation of FÃ¶rster resonance energy transfer between two optically nonlinear cyanine dyes of small Stokes shift energies in polymer thin films. Journal of Applied Physics, 2011, 110, 083521.	1.1	5
117	Bound biexciton luminescence in nitrogen Î´â€doped GaAs. Physica Status Solidi (B): Basic Research, 2011, 248, 464-467.	0.7	7
118	Propagation velocity of excitonic polaritons confined in GaAs thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 378-380.	0.8	3
119	Energy band structure and the halfâ€filling of the intermediate band in the quantumâ€dot solar cell. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 622-624.	0.8	5
120	Interaction between conductionâ€band edge and nitrogenâ€related localized levels in nitrogen Î´ â€doped GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 365-367.	0.8	1
121	Broadband light sources using InAs quantum dots with InGaAs strain-reducing layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 331-333.	0.8	14
122	Optical and ferromagnetic properties of GdN thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 488-490.	0.8	7
123	Intraband relaxation process in highly stacked quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 46-49.	0.8	4
124	Excitation power dependence of nonlinear optical response of excitons in GaAs/AlAs superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 50-53.	0.8	2
125	Optical and magnetic properties in epitaxial GdN thin films. Physical Review B, 2011, 83, .	1.1	49
126	Depolarization effect on optical control of exciton states confined in GaAs thin films. Journal of Applied Physics, 2011, 110, 043514.	1.1	3

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127	Experimental and atomistic theoretical study of degree of polarization from multilayer InAs/GaAs quantum dot stacks. Physical Review B, 2011, 84, .	1.1	45
128	Dynamics of above-barrier state excitons in multi-stacked quantum dots. Journal of Applied Physics, 2011, 110, 093515.	1.1	4
129	Observation of phase shifts in a vertical cavity quantum dot switch. Applied Physics Letters, 2011, 98, 231101.	1.5	20
130	Influence of local atomic configuration in AlGdN phosphor thin films on deep ultra-violet luminescence intensity. Journal of Applied Physics, 2011, 110, 093108.	1.1	7
131	Field-emission properties of carbon nanotube composite in side-electron emission configuration. Journal of Applied Physics, 2011, 109, 074307.	1.1	5
132	Ultraviolet Light Emitting Devices Using AlGdN. Materials Research Society Symposia Proceedings, 2011, 1342, 55.	0.1	0
133	Two-photons transition in intermediate band solar cells. , 2011, , .		0
134	Multidirectional Observation of Photoluminescence Polarization Anisotropy in Closely Stacked InAs/GaAs Quantum Dots. Applied Physics Express, 2011, 4, 062001.	1.1	39
135	Dephasing of Excitonic Polaritons Confined in GaAs Thin Films. Journal of the Physical Society of Japan, 2011, 80, 034704.	0.7	3
136	Vertical stacking of InAs quantum dots for polarization-insensitive semiconductor optical amplifiers. Journal of Physics: Conference Series, 2010, 245, 012076.	0.3	5
137	Spatially Resolved Thermal Conductivity of Intermetallic Compounds Measured by Micro-Thermoreflectance Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2010, 74, 740-745.	0.2	5
138	Detailed Design and Characterization of All-Optical Switches Based on InAs/GaAs Quantum Dots in a Vertical Cavity. IEEE Journal of Quantum Electronics, 2010, 46, 1582-1589.	1.0	14
139	Highly Efficient Ultra-Violet Luminescence from Low-Temperature Grown AlGdN. Zairyo/Journal of the Society of Materials Science, Japan, 2010, 59, 666-670.	0.1	0
140	Temperature dependence of photoluminescence characteristics of excitons in stacked quantum dots and quantum dot chains. Journal of Applied Physics, 2010, 107, 073506.	1.1	13
141	Effects of absorption coefficients and intermediate-band filling in InAs/GaAs quantum dot solar cells. Applied Physics Letters, 2010, 97, .	1.5	43
142	Intraband relaxation of photoexcited carriers in multiple stacked quantum dots and quantum dot chains. , 2010, , .		0
143	Statistical fluctuation of magnetization in Mn-composition modulated Cd1â^'xMnxTe quantum wires. Journal of Applied Physics, 2010, 107, 043521.	1.1	1
144	All-optical switch using InAs quantum dots in a vertical cavity. , 2010, , .		1

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145	Polarization control of electroluminescence from vertically stacked InAs/GaAs quantum dots. Applied Physics Letters, 2010, 96, .	1.5	33
146	Impurity doping in self-assembled InAs/GaAs quantum dots by selection of growth steps. Journal of Applied Physics, 2010, 108, .	1.1	31
147	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. Applied Physics Letters, 2010, 96, 151104.	1.5	22
148	Multi-stacked InAs/GaNAs quantum dots with direct Si doping for use in intermediate band solar cell. , 2010, , .		8
149	Vertically stacked InAs quantum dots for polarization-independent semiconductor optical amplifiers. Proceedings of SPIE, 2010, , .	0.8	6
150	Energy band structure and absorption coefficients in the quantum-dot intermediate band solar cells. , 2010, , .		1
151	Exciton response controlled by introducing a spacer layer in nitrided InAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S146.	0.8	1
152	Transient reflectivity response with negative time delay caused by femtosecond pulse propagation in GaAs thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S139-S142.	0.8	3
153	Side electron emission device using a composite of carbon nanofibers and aluminum. Thin Solid Films, 2009, 518, 530-533.	0.8	4
154	Anisotropic linear-polarization luminescence in CdTe/CdMnTe quantum wires. Journal of Luminescence, 2009, 129, 1448-1453.	1.5	0
155	Quantum dots in a vertical cavity for all-optical switching devices. , 2009, , .		0
156	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. Applied Physics Letters, 2009, 95, 021109.	1.5	39
157	Analysis of thermoreflectance signals and characterization of thermal conductivity of metal thin films. Review of Scientific Instruments, 2009, 80, 124901.	0.6	15
158	Thermal Conductivity Measurement Technique for Cu-Pt Alloy Thin Films by a Modulated Thermoreflectance Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2009, 73, 434-438.	0.2	7
159	Narrowband ultraviolet field-emission device using Gd-doped AlN. IOP Conference Series: Materials Science and Engineering, 2009, 1, 012001.	0.3	10
160	Photoluminescence dynamics of coupled quantum dots. Journal of Luminescence, 2008, 128, 975-977.	1.5	7
161	Anisotropic magneto-optical effects inCdTe/Cd0.75Mn0.25Tequantum wire structures. Physical Review B, 2008, 78, .	1.1	3
162	Real time analysis of self-assembled InAs/GaAs quantum dot growth by probing reflection high-energy electron diffraction chevron image. Journal of Applied Physics, 2008, 104, 074305.	1.1	20

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163	Exciton fine structure of nitrogen isoelectronic centers in GaAs. , 2008, , .		0
164	Effects of indium segregation on optical properties of nitrogen-doped InAs/GaAs quantum dots. Journal of Applied Physics, 2008, 104, 103532.	1.1	4
165	Photoluminescence characteristics of quantum dots with electronic states interconnected along growth direction. Journal of Applied Physics, 2008, 103, .	1.1	42
166	Fine structure splitting of isoelectronic bound excitons in nitrogen-doped GaAs. Physical Review B, 2008, 77, .	1.1	20
167	Side electron emission device using carbon nanofiber/elastomer composite sheet. Applied Physics Letters, 2008, 92, .	1.5	15
168	Electron tomography of embedded semiconductor quantum dot. Applied Physics Letters, 2008, 92, .	1.5	42
169	Dual chopped photoreflectance spectroscopy for nondestructive characterization of semiconductors and semiconductor nanostructures. Review of Scientific Instruments, 2008, 79, 046110.	0.6	12
170	Narrow-band deep-ultraviolet light emitting device using Al1â^'xGdxN. Applied Physics Letters, 2008, 93, .	1.5	15
171	Multidirectional observation of an embedded quantum dot. Applied Physics Letters, 2007, 90, 041911.	1.5	13
172	Multidirectional Transmission Electron Microscope Observation of a Single InAs/GaAs Self-Assembled Quantum Dot. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
173	Control of Optical Emission from Coupled Excitonic States in Quantum Dot Superlattice Structures. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
174	Real Time Probing of Self-Assembling Process Steps in InAs/GaAs Quantum Dot Growth. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
175	Anisotropic Magnetic-Field Evolution of Valence-Band States in One-Dimensional Diluted Magnetic Semiconductors. AIP Conference Proceedings, 2007, , .	0.3	0
176	Emission-wavelength extension of nitrided InAs/GaAs quantum dots with different sizes. Journal of Crystal Growth, 2007, 301-302, 709-712.	0.7	3
177	Atomically controlled doping of nitrogen on GaAs(001) surfaces. Journal of Crystal Growth, 2007, 301-302, 34-37.	0.7	7
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